device uses patent-pending circuit topologies to

## FEATURES

- Low Insertion Loss: 0.8 dB at 2 GHz
- High Isolation: > 25 dB
- Low Harmonic Levels: <-65 dBc at max. GSM
power
- Low Control Voltage Operation: to +2.5 V


## APPLICATIONS

- Front-end Modules for GSM Wireless Handsets



## PRODUCT DESCRIPTION

The AWS5524 is a single pole, four throw (SP4T) RF switch developed to meet the stringent requirements of GSM systems. Manufactured in ANADIGICS' state-of-the-art pHEMT process, the
provide the low insertion loss, high port-to-port isolation and high linearity needed to enhance the performance of GSM radios. The AWS5524 is offered as an unpackaged MMIC die.


Figure 1: Block Diagram


Dimensions in $\mu \mathrm{m}$ Bond Pads: $100 \mu \mathrm{~m} \times 75 \mu \mathrm{~m}$

Die Thickness: $178 \mu \mathrm{~m}$
Figure 2: Die Configuration

Table 1: Pad Description

| NAME | DESCRIPTION | NAME | DESCRIPTION |
| :---: | :--- | :---: | :--- |
| RF1 | RF port, path 1 | RF3 | RF port, path 3 |
| RFG1 | Ground | RFG3 | Ground |
| V1 | Control voltage, RF path 1 | V3 | Control voltage, RF path 3 |
| V2 | Control voltage, RF path 2 | V4 | Control voltage, RF path 4 |
| RFG2 | Ground | RF4G | Ground |
| RF2 | RF port, path 2 | RF4 | RF port, path 4 |
| VS | Common port bias <br> voltage (logic high) | RFC | RF common port |

## ELECTRICAL CHARACTERISTICS

Table 2: Absolute Minimum and Maximum Ratings

| PARAMETER | MIN | MAX | UNIT | COMMENTS |
| :--- | :---: | :---: | :---: | :--- |
| Common Port Bias Voltage $\left(\mathrm{V}_{\text {s }}\right)^{(1)}$ | -0.2 | +8.0 | V |  |
| Control Voltages $\left(\mathrm{V}_{1}, \mathrm{~V}_{2}, \mathrm{~V}_{3}, \mathrm{~V}_{4}\right)$ | -0.2 | +8.0 | V |  |
| RF Input Power $\left(\mathrm{P}_{\mathrm{N}}\right)$ | - | 10 | W | at all RF ports |
| Storage Temperature ${ }^{(2)}$ | -65 | +150 | ${ }^{\circ} \mathrm{C}$ |  |

Stresses in excess of the absolute ratings may cause permanent damage. Functional operation is not implied under these conditions. Exposure to absolute ratings for extended periods of time may adversely affect reliability.
Notes:
(1) The VS port may remain open-circuited without damage to the device.
(2) Storage Temperature limits apply to the die only after it has been removed from the ANADIGICS shipping material.
3. All RF ports should be AC-coupled. No external DC bias should be applied.

Table 3: Operating Ranges

| PARAMETER | MIN | TYP | MAX | UNIT | COMMENTS |
| :---: | :---: | :---: | :---: | :---: | :---: |
| RF Frequency (f) | 0.5 | - | 2.5 | GHz |  |
| Common Port Bias Voltage (Vs) | - | (1) | - | - | applied at VS port |
| Control Voltages ( $\mathrm{V}_{1}, \mathrm{~V}_{2}, \mathrm{~V}_{3}, \mathrm{~V}_{4}$ ) | $\begin{gathered} 0 \\ +2.5 \end{gathered}$ | - | $\begin{aligned} & +0.2 \\ & +3.5 \end{aligned}$ | V | RF path OFF state RF path ON state |
| Ambient Temperature ( $\mathrm{T}_{\mathrm{A}}$ ) | -30 | - | +85 | ${ }^{\circ} \mathrm{C}$ |  |

The device may be operated safely over these conditions; however, parametric performance is guaranteed only over the conditions defined in the electrical specifications.
Notes:
(1) For optimal linearity performance, the Common Port Bias Voltage ( $V$ s) should be set to the same Control Voltage used to turn ON any of the individual RF paths. The VS port may remain open-circuited without damage to the device, but with some degradation in linearity.

Table 4: Electrical Specifications
( $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$; RF ports terminated with $50 \Omega$; $\mathrm{V}_{\mathrm{n}}=+2.7 \mathrm{~V}$ and is the Control Voltage for the ON path, RFC - RFn; $\mathrm{V}_{\mathrm{x}}=0 \mathrm{~V}$ and is the Control Voltage for the OFF paths, RFC - RFx)

| PARAMETER | MIN | TYP | MAX | UNIT | COMMENTS |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\begin{aligned} & \text { Insertion Loss } \\ & 1 \mathrm{GHz} \\ & 2 \mathrm{GHz} \end{aligned}$ | - | $\begin{aligned} & 0.5 \\ & 0.8 \end{aligned}$ | $\begin{aligned} & 0.7 \\ & 1.0 \end{aligned}$ | dB | RFC port to selected RFn port |
| $\begin{aligned} & \text { Return Loss }{ }^{(1)} \\ & 1 \mathrm{GHZ} \\ & 2 \mathrm{GHz} \end{aligned}$ |  | $\begin{aligned} & -25 \\ & -17 \end{aligned}$ | $\begin{aligned} & -20 \\ & -15 \end{aligned}$ | dB | RFC port and selected RFn port |
| Isolation <br> 1 GHz <br> 2 GHz | $\begin{aligned} & 25 \\ & 25 \end{aligned}$ | 27 27 | - | dB | RFC port to isolated RFx ports |
| Input Third Order Intercept ${ }^{(2)}$ 800 MHz Cellular Band 1900 MHz PCS Band |  | $\begin{aligned} & +66 \\ & +59 \end{aligned}$ |  | dBm | RFC port to selected RFn port |
| 2nd Harmonic Rejection $\begin{aligned} & 1 \mathrm{GHz} \\ & 2 \mathrm{GHz} \end{aligned}$ | - | $\begin{aligned} & -71 \\ & -72 \end{aligned}$ | $\begin{aligned} & -65 \\ & -65 \end{aligned}$ | dBc | RFC port to selected RFn port $\begin{aligned} & P_{\mathbb{N}}=+34 \mathrm{dBm} \\ & P_{\mathbb{N}}=+32 \mathrm{dBm} \end{aligned}$ |
| 3rd Harmonic Rejection ${ }^{(3)}$ $1 \mathrm{GHz}$ $2 \mathrm{GHz}$ | - | $\begin{aligned} & -88 \\ & -80 \end{aligned}$ | $\begin{aligned} & -65 \\ & -65 \end{aligned}$ | dBc | RFC port to selected RFn port $\begin{aligned} & P_{\mathbb{N}}=+34 \mathrm{dBm} \\ & P_{\mathbb{N}}=+32 \mathrm{dBm} \end{aligned}$ |
| Current Consumption | - | - | $\begin{gathered} 30 \\ 5 \end{gathered}$ | $\begin{aligned} & \mu \mathrm{A} \\ & \mu \mathrm{~A} \end{aligned}$ | each Vn port VS port |

Notes:
(1) Isolated RFx ports have a return loss of approximately -3 dB .
(2) For the Cellular Band, two tones with $P_{N}=+22.5 \mathrm{dBm}$ each, at 837 and 838 MHz . For the PCS Band, two tones with $P_{N}=+21$ dBm each, at 1880 and 1881 MHz .
(3) $V_{s}=V_{n}$

Table 5: Switch Control Truth Table

| CONTROL <br> VOLTAGES | $\mathbf{V}_{1}$ | +2.5 to +3.5 V | 0 to +0.2 V | 0 to +0.2 V | 0 to +0.2 V |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | $\mathbf{V}_{2}$ | 0 to +0.2 V | +2.5 to +3.5 V | 0 to +0.2 V | 0 to +0.2 V |
|  | $\mathbf{V}_{3}$ | 0 to +0.2 V | 0 to +0.2 V | +2.5 to +3.5 V | 0 to +0.2 V |
| RF PATH <br> SELECTION | $\mathbf{V}_{4}$ | 0 to +0.2 V | 0 to +0.2 V | 0 to +0.2 V | +2.5 to +3.5 V |
|  | RFC - RF1 | RFC - RF2 | ON | OFF | OFF |
|  | OFF | ON | OFF |  |  |
|  | RFC - RF4 | OFF | OFF | OFF | OFF |

## PERFORMANCE DATA

Figure 3: Insertion Loss vs. Frequency ( ON path, $\mathrm{V}_{\mathrm{n}}=+2.7 \mathrm{~V}, \mathrm{~V}_{\mathrm{x}}=0 \mathrm{~V}$ )


Figure 5: Return Loss vs. Frequency
( ON path, $\mathrm{V}_{\mathrm{n}}=+2.7 \mathrm{~V}, \mathrm{~V}_{\mathrm{x}}=0 \mathrm{~V}$ )


Figure 4: Harmonics of 1 GHz vs. Control Voltage (ON path, $\mathrm{V}_{\mathrm{x}}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{GHz}, \mathrm{P}_{\text {IN }}=+34 \mathrm{dBm}$ )


Figure 6: Harmonics of 2 GHz vs. Control Voltage ( ON path, $\mathrm{V}_{\mathrm{x}}=0 \mathrm{~V}, \mathrm{f}=2 \mathrm{GHz}, \mathrm{P}_{\mathrm{IN}}=+32 \mathrm{dBm}$ )


Figure 7: Isolation vs. Frequency (OFF path, $\mathrm{V}_{\mathrm{n}}=+2.7 \mathrm{~V}, \mathrm{~V}_{\mathrm{x}}=0 \mathrm{~V}$ )


## AWS5524

## APPLICATION INFORMATION

## Die Applications

Bonding and circuit connections for the unpackaged AWS5524 die are shown in Figure 8, and application details are listed in the following notes:

1. Cb are DC blocking capacitors external to the device. A value of 100 pF is sufficient for operation to 500 MHz . The values may be tailored to provide specific electrical responses. The isolation of the switch provides enough decoupling of RF ports 1 through 4 so that overall switch performance is not affected.
2. The VS pin provides a fixed voltage potential to the common port of the switch. To get the best linear performance, it should be tied to the logic high voltage potential (not the power supply). Current draw on this pin is less than $5 \mu \mathrm{~A}$.
3. The RF Ground bondwires should be kept as short as possible and bonded directly to a good RF ground for best broadband performance.
4. Lesd provides a means to increase the ESD protection on a specific RF port, typically the port attached to the antenna. The ESD rating of the device is $\pm 125 \mathrm{~V}$ HBM overall. This rating is associated with the control pin to RF port path. RF port to RF port/RF Gnd has been determined to be $> \pm 500 \mathrm{~V}$ HBM for this technology. By using Lesd as an RF choke on a port, an ESD protection to $\pm 8 \mathrm{kV}$ contact discharge can be achieved.
5. The die may be attached by either conductive or non-conductive epoxy formulated for attaching semiconductor parts. The back of the die is electrically isolated from the switch circuit and can be grounded or left isolated.


Figure 8: Application Schematic

| ORDER NUMBER | TEMPERATURE <br> RANGE | PACKAGE <br> DESCRIPTION | COMPONENT PACKAGING |
| :---: | :---: | :---: | :---: |
| AWS5524D1 | $-30^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | Die | (contact ANADIGICS for details) |

## VANADIGICS

## ANADIGICS, Inc.

141 Mount Bethel Road
Warren, New Jersey 07059, U.S.A.
Tel: +1 (908) 668-5000
Fax: +1 (908) 668-5132
URL: http://www.anadigics.com
E-mail: Mktg@anadigics.com

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